Schottky barrier single diodes Rev. 01 — 21 May 2007

Product data sheet

1. Product profile

1.1 General description

Planar Schottky barrier single diodes with an integrated guard ring for stress protection, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number	Package	Package		
	NXP	JEITA	configuration	
RB751CS40	SOD882	-	leadless ultra small	
RB751S40	SOD523	SC-79	ultra small	
RB751V40	SOD323	SC-76	very small	

1.2 Features

- Low forward voltage
- Low capacitance

1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Line termination
- Reverse polarity protection

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		-	-	120	mA
V _{RRM}	repetitive peak reverse voltage		-	-	40	V
V _F	forward voltage	I _F = 1 mA	<u>[1]</u> _	-	370	mV

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



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2. Pinning information

Pin	Description	Simplified outline Symbol
SOD882		
1	cathode	[1]
2	anode	
		sym001
		Transparent top view
SOD323;	SOD523	
1	cathode	[1]
2	anode	
		1 2 sym001
		001aab540

[1] The marking bar indicates the cathode.

3. Ordering information

Type number	Package		
	Name	Description	Version
RB751CS40	-	leadless ultra small plastic package; 2 terminals; body $1.0 \times 0.6 \times 0.5$ mm	SOD882
RB751S40	SC-79	plastic surface-mounted package; 2 leads	SOD523
RB751V40	SC-76	plastic surface-mounted package; 2 leads	SOD323

4. Marking

Table 5. Marking codes

Type number	Marking code
RB751CS40	F6
RB751S40	G4
RB751V40	W8

5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	40	V
V _R	reverse voltage		-	40	V
I _F	forward current		-	120	mA
I _{FSM}	non-repetitive peak forward current	square wave; t _p < 10 ms	-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u>		
	RB751CS40		[2] _	250	mW
	RB751S40		[2] _	280	mW
	RB751V40		-	280	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Thermal characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
thermal resistance from junction to ambient	in free air	<u>[1]</u>			
RB751CS40		[2] _	-	500	K/W
RB751S40		[2] _	-	450	K/W
RB751V40		-	-	450	K/W
	Parameterthermal resistance from junction to ambientRB751CS40RB751S40	ParameterConditionsthermal resistance from junction to ambientin free airRB751CS40RB751S40	ParameterConditionsMinthermal resistance from junction to ambientin free air[1]RB751CS40[2]-RB751S40[2]-	ParameterConditionsMinTypthermal resistance from junction to ambientin free air[1]RB751CS40[2]RB751S40[2]	ParameterConditionsMinTypMaxthermal resistance from junction to ambientin free air[1]

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

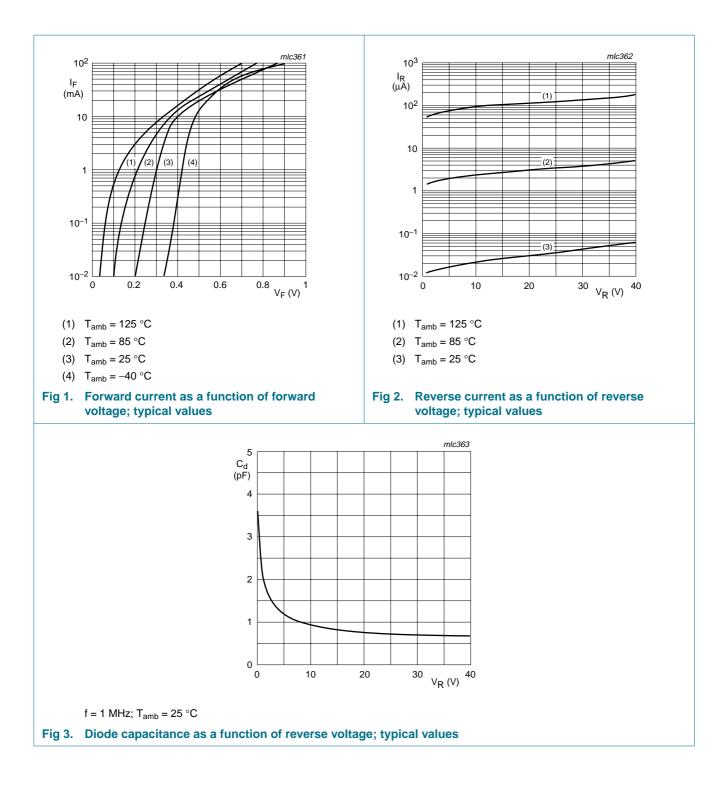
Table 8.Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	I _F = 1 mA	<u>[1]</u> _	-	370	mV
I _R	reverse current	V _R = 30 V	-	-	0.5	μΑ
C _d	diode capacitance	V _R = 1 V; f = 1 MHz	-	2	-	pF

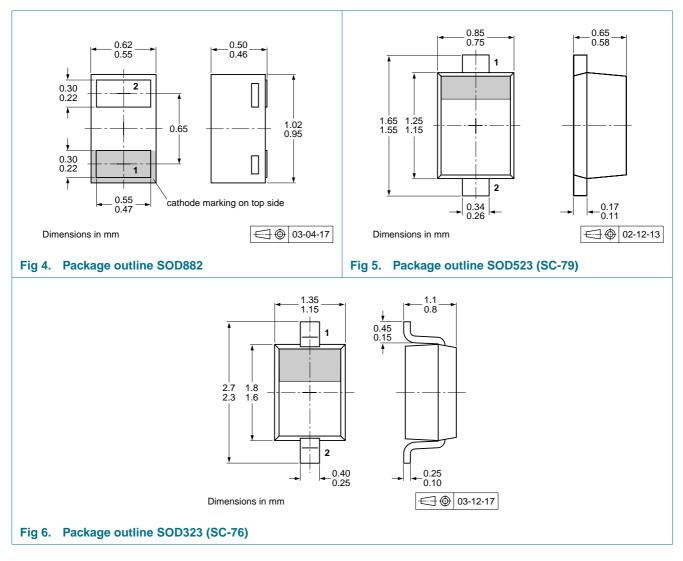
[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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8. Package outline



9. Packing information

Table 9.Packing methods

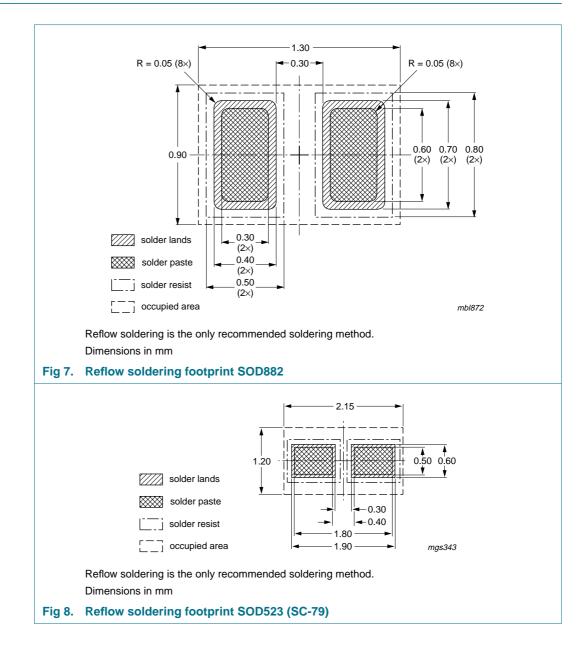
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packin	Packing quantity		
			3000	8000	10000	
RB751CS40	SOD882	2 mm pitch, 8 mm tape and reel	-	-	-315	
RB751S40	RB751S40 SOD523	2 mm pitch, 8 mm tape and reel	-	-315	-	
		4 mm pitch, 8 mm tape and reel	-115	-	-135	
RB751V40	SOD323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

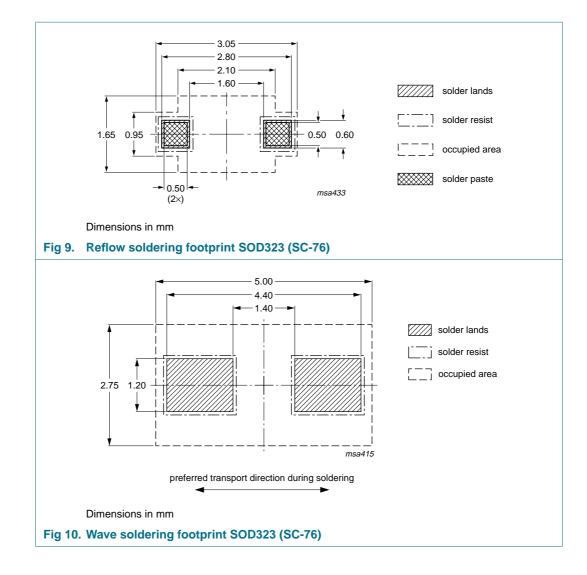
[1] For further information and the availability of packing methods, see <u>Section 13</u>.

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10. Soldering



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RB751_SER_1 Product data sheet

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11. Revision history

Table 10. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
RB751_SER_1	20070521	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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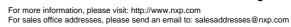
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